ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE5608 thru NTE5610
TRIAC
8 Amp

Description:

The NTE5608 through NTE5610 series of TRIACs are high performance glass passivated PNPN devices in a TO220 type package designed for general purpose applications where moderate gate sensitivity is required.

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Repetitive Peak Off–State Voltage (T_J = –40° to +125°C, R_{GK} = 1kΩ), V_{DRM}
- NTE5608 . . . . . 400V
- NTE5609 . . . . . 600V
- NTE5610 . . . . . 800V

On–State Current (All Conduction Angles, T_C = +85°C), $I_{T(RMS)}$ 8A

Non–Repetitive On–State Current (Half Cycle), I_{TSM}
- 60Hz 77A
- 50Hz 70A

Fusing Current (t = 10ms), I^2t . . . . . $24A^2s$

Peak Gate Current (t = 10μs Max), I_{GM} 4A

Peak Gate Dissipation (t = 10μs Max), P_{GM} 10W

Gate Dissipation (t = 20ms Max), $P_{G(AV)}$ 1W

Operating Junction Temperature Range, T_J . . . . . –40° to +125°C

Storage Temperature Range, T_{stg} . . . . . –40° to +125°C

Thermal Resistance, Junction–to–Case, R_{thJC} 3K/W

Thermal Resistance, Junction–to–Ambient, R_{thJA} 60K/W

Lead Temperature (During Soldering, 1.6mm from case, 10sec max), T_L . . . . . +250°C

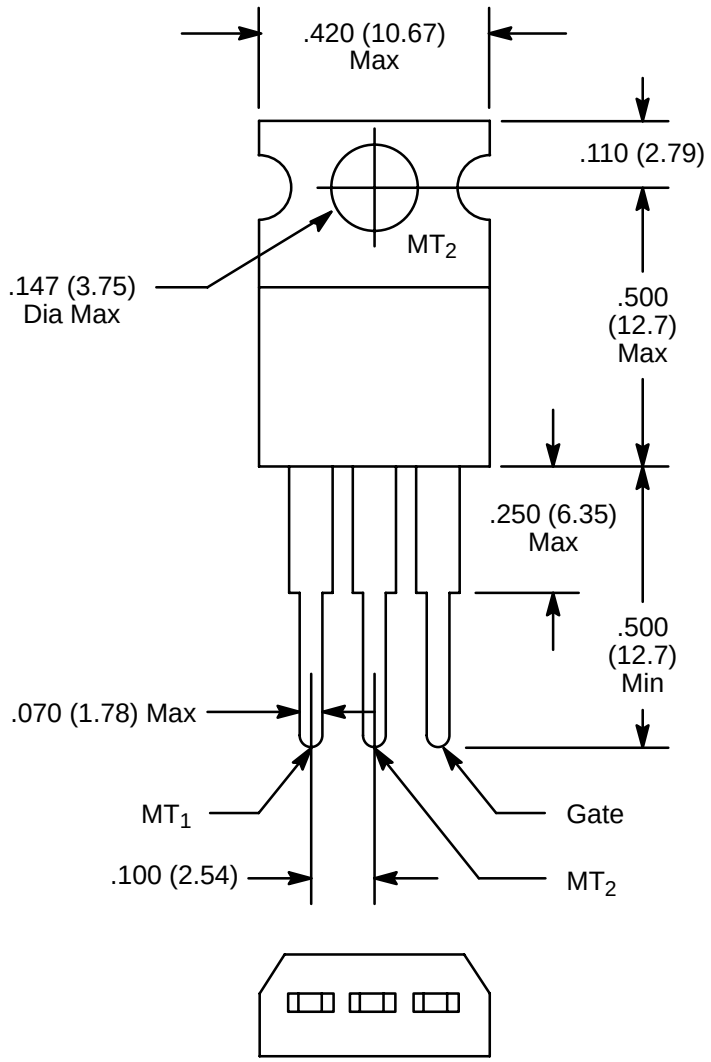
Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off–State Leakage Current	I_{DRM}	$V_D = V_{DRM}$, R_{GK} = 1kΩ, T_J = +25°C	–	–	5	μA
		$V_D = V_{DRM}$, R_{GK} = 1kΩ, T_J = +125°C	–	–	2	mA
On–State Voltage	V_T	I_T = 12A, T_J = +25°C	–	–	1.85	V
On–State Threshold Voltage	$V_{T(TO)}$	T_J = +125°C	–	–	1	V
On–State Slope Resistance	r_T	T_J = +125°C	–	–	80	mΩ

Electrical Characteristics (Cont'd): (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Gate Trigger Current	I_{GT}	V_D = 12V, Note 1	–	–	10	mA
Gate Trigger Voltage	V_{GT}	V_D = 12V, All Quadrants	–	–	2.5	V
Holding Current	I_H	R_{GK} = 1kΩ	–	–	10	mA
Critical Rate–of–Rise	dv/dt	V_D = 0.67 x V_{DRM}, R_{GK} = 1kΩ, T_J = +125°C	50	–	–	V/µs
Critical Rate–of–Rise, Off–State	dv/dt_c	I_T = 8A, di/dt = 3.55A/ms, T_C = +85°C	2	–	–	V/µs

Note 1. For either polarity of gate voltage with reference to electrode MT_1.



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